

L Number	Hits	Search Text	DB	Time stamp
1	2322	cladding with buffer with layer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/05 13:46
2	1260	cladding with buffer with layer with act\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/05 13:47
3	257	(cladding with buffer with layer with act\$3) and 438/\$3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/05 13:47
4	29	cladding with buffer with layer with (act or acting)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/05 13:54
5	7	form\$3 with superlattice with buffer with (over or on) with (semiconductor or "gan")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/05 13:59
6	5	form\$3 with grad\$3 with buffer with (over or on) with (semiconductor or "gan")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/05 15:03
7	6	form\$3 with multiple with buffer with (over or on) with (semiconductor or "gan")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/05 15:03
-	209	(fabricat\$3 with gan with substrate) and (crack or fault or defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/05 13:45
-	147	((fabricat\$3 with gan with substrate) and (crack or fault or defect)) and (buffer with gan)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 15:39
-	17	(((((fabricat\$3 with gan with substrate) and (crack or fault or defect)) and (buffer with gan)) and ((buffer with first) and (buffer with second))) and @ad<20010305	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 15:42
-	70	(sapphire with substrate) and (crack or fault or defect) and ((upper or second or first) with buffer with gan) and (lower with buffer with gan)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 16:46
-	36	((sapphire with substrate) and (crack or fault or defect) and ((upper or second or first) with buffer with gan) and (lower with buffer with gan)) and @ad<20010305	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 16:04
-	1	((sapphire with substrate) and (crack or fault or defect) and ((upper or second or first) with buffer with gan) and (lower with buffer with gan)) and (gan with semiconductor with substrate with fabrication)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 16:02
-	22	gan with semiconductor with substrate with fabrication	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 16:04
-	15	(gan with semiconductor with substrate with fabrication) and @ad<20010305	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 17:10
-	118	(sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with gan))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 16:48

	3	((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with gan))) and (dichlorosilane or "sih.sub.2cl.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 18:42
	4	(gan with semiconductor with substrate with fabrication) and ((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with gan)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 16:52
	35	((fabricat\$3 with gan with substrate) and (crack or fault or defect)) and (buffer with gan)) and ((buffer with first) and (buffer with second))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 16:54
	3	((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with gan))) and (((fabricat\$3 with gan with substrate) and (crack or fault or defect)) and (buffer with gan)) and ((buffer with first) and (buffer with second)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 16:58
	566	(buffer with ((multi adj layer) or (multiple adj layer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 18:06
	5	((sapphire with substrate) and (crack or fault or defect) and ((silicon with dop\$3 with buffer) or (silicon with dop\$3 with gan))) and ((buffer with ((multi adj layer) or (multiple adj layer))))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 17:01
	25	(buffer with ((multi adj layer) or (multiple adj layer)) with dop\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 17:10
	19	((buffer with ((multi adj layer) or (multiple adj layer)) with dop\$3)) and @ad<20010305	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 17:13
	2	(gan with semiconductor with substrate with fabrication) and ((buffer with ((multi adj layer) or (multiple adj layer))))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 17:12
	42	((buffer with ((multi adj layer) or (multiple adj layer)))) and gan and sapphire	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 17:13
	27	((buffer with ((multi adj layer) or (multiple adj layer)))) and gan and sapphire) and @ad<20010305	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 18:57
	0	((buffer with ((multi adj layer) or (multiple adj layer))) same gradient same dop\$3) and gan	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 17:58
	0	((buffer same ((multi adj layer) or (multiple adj layer))) same gradient same dop\$3) and gan	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 17:58
	0	((buffer same ((multi adj layer) or (multiple adj layer))) same gradient) and gan	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 17:59
	7	buffer same gan same gradient	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 18:05
	148	(buffer same gradient) and gan	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 18:24

-	0	((buffer with ((multi adj layer) or (multiple adj layer)) with dop\$3)) and ((buffer same gradient) and gan)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 18:05
-	0	((buffer with ((multi adj layer) or (multiple adj layer)))) and ((buffer same gradient) and gan)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 18:05
-	3	(buffer with ((multi adj layer) or (multiple adj layer))) and (buffer same concentration same gradient)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 18:23
-	213	buffer with layer with gradient	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 18:49
-	12	(buffer with layer with gradient) and gan	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 18:49
-	5	buffer with (dichlorosilane or "sih.sub.2cl.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 18:43
-	531	(buffer with layer) same gradient	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 18:49
-	22	((buffer with layer) same gradient) and gan	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 18:57
-	209	super with lattice with dop\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 18:57
-	19	(super with lattice with dop\$3) same gan	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 18:57
-	12	((super with lattice with dop\$3) same gan) and @ad<20010305	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 19:09
-	10	((super with lattice with dop\$3) same gan) and @ad<20010305) and buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 19:07
-	44	(first adj buffer) and (second adj buffer) and concentration and symmetrical	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 19:35
-	39	((first adj buffer) and (second adj buffer) and concentration and symmetrical) and @ad<20010305	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 20:09
-	181	(first adj buffer) and (second adj buffer) and concentration and gradient	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 19:37
-	22	((first adj buffer) and (second adj buffer) and concentration and gradient) and (438/\$3.ccls. or 257/\$3.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 20:06
-	526	(buffer with dop\$3 with concentration) and (438/\$3.ccls. or 257/\$3.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 20:21
-	66	((buffer with dop\$3 with concentration) and (438/\$3.ccls. or 257/\$3.ccls.)) and (buffer with multi\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 20:08

-	66	((buffer with dop\$3 with concentration) and (438/\$3.ccls. or 257/\$3.ccls.)) and (buffer with multi\$3 with layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 20:21
-	53	((buffer with dop\$3 with concentration) and (438/\$3.ccls. or 257/\$3.ccls.)) and (buffer with multi\$3 with layer) and @ad<20010305	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 20:52
-	89	method with fabricat\$3 with gan with substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 20:16
-	5	((buffer with dop\$3 with concentration) and (438/\$3.ccls. or 257/\$3.ccls.)) and (method with fabricat\$3 with gan with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 20:16
-	12	(buffer with dop\$3 with concentration) same (buffer with multiple with layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 20:39
-	0	(buffer with dop\$3 with profile) same (buffer with multiple with layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 20:38
-	2	(buffer with increas\$3 with concentration) same (buffer with multiple with layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 20:40
-	4	(buffer with increas\$3 with dop\$3) same (buffer with multiple with layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 20:42
-	8	buffer with doping with concentration with profile	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 20:45
-	14	buffer with dop\$3 with gradient	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 20:51
-	826	buffer with dop\$3 with concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 20:52
-	165	(buffer with dop\$3 with concentration) and gan	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 20:52
-	45	((buffer with dop\$3 with concentration) and gan) and 438/\$3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 21:09
-	31	((buffer with dop\$3 with concentration) and gan) and 438/\$3.ccls.) and @ad<20010305	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 21:09
-	89	buffer with doped with undoped with gan	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 21:09
-	61	(buffer with doped with undoped with gan) and @ad<20010305	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 21:09
-	13	((buffer with doped with undoped with gan) and @ad<20010305) and 438/\$3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/13 21:09
-	140582	(substrate with sapphire or (silicon adj carbide) or "al.sub.2o.sub.3" or "sic")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 15:43

-	2080	(buffer with (over or on) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 15:44
-	1190	((semiconductor or "gan") with (on or over) with buffer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 15:45
-	418296	((remov\$3 or thin\$4 etch\$3) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 15:45
-	295	((substrate with sapphire or (silicon adj carbide) or "al.sub.2o.sub.3" or "sic")) and ((buffer with (over or on) with substrate)) and (((semiconductor or "gan") with (on or over) with buffer)) and (((remov\$3 or thin\$4 etch\$3) with substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 15:46
-	12	((substrate with sapphire or (silicon adj carbide) or "al.sub.2o.sub.3" or "sic")) same ((buffer with (over or on) with substrate)) same (((semiconductor or "gan") with (on or over) with buffer)) same (((remov\$3 or thin\$4 etch\$3) with substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 15:48
-	8	((substrate with sapphire or (silicon adj carbide) or "al.sub.2o.sub.3" or "sic")) same ((buffer with (over or on) with substrate)) same (((semiconductor or "gan") with (on or over) with buffer)) same (((remov\$3 or thin\$4 etch\$3) with substrate)) and (@ad<20010305 or @rlad<20010305)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 15:59
-	55	((substrate with sapphire or (silicon adj carbide) or "al.sub.2o.sub.3" or "sic")) and ((buffer with (over or on) with substrate)) and (((semiconductor or "gan") with (on or over) with buffer)) and (((remov\$3 or thin\$4 etch\$3) with substrate)) and (second with buffer with (semiconductor or "gan"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 15:59
-	30	((substrate with sapphire or (silicon adj carbide) or "al.sub.2o.sub.3" or "sic")) and ((buffer with (over or on) with substrate)) and (((semiconductor or "gan") with (on or over) with buffer)) and (((remov\$3 or thin\$4 etch\$3) with substrate)) and (second with buffer with (semiconductor or "gan")) and (@ad<20010305 or @rlad<20010305)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 17:27
-	1	form\$3 with buffer with stress with base with main with substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 17:25
-	115	form\$3 with buffer with stress with (semiconductor or "gan") with (substrate or sapphire or (silicon adj carbide) or "al.sub.2o.sub.3" or "sic")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 17:26
-	51	(form\$3 with buffer with stress with (semiconductor or "gan") with (substrate or sapphire or (silicon adj carbide) or "al.sub.2o.sub.3" or "sic")) and (second with buffer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 17:27
-	36	((form\$3 with buffer with stress with (semiconductor or "gan") with (substrate or sapphire or (silicon adj carbide) or "al.sub.2o.sub.3" or "sic")) and (second with buffer)) and (@ad<20010305 or @rlad<20010305)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 19:21



157	((form\$3 with buffer with (over or on) with (semiconductor or "gan") with (substrate or sapphire or (silicon adj carbide) or "al.sub.2o.sub.3" or "sic")) and (second with buffer)) and (@ad<20010305 or @rlad<20010305)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 19:58
75	((form\$3 with buffer with (over or on) with (semiconductor or "gan") with (substrate or sapphire or (silicon adj carbide) or "al.sub.2o.sub.3" or "sic")) and (second with buffer)) and (@ad<20010305 or @rlad<20010305)) and (remov\$3 with (substrate or sapphire or (silicon adj carbide) or "al.sub.2o.sub.3" or "sic"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 19:23
68	(form\$3 with buffer with (over or on) with "gan") and (@ad<20010305 or @rlad<20010305)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/04 19:59